
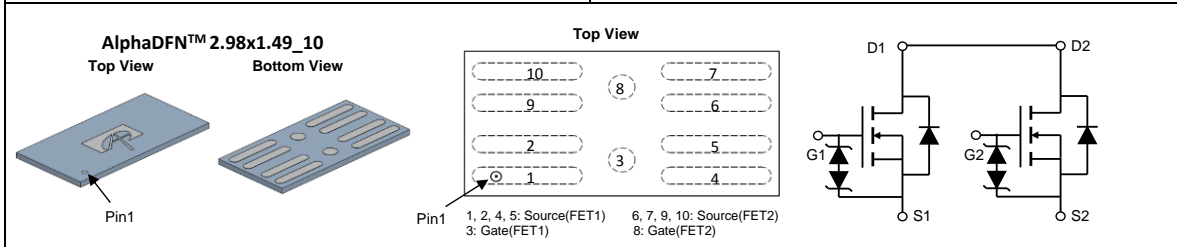


# AOCA33104E

## 12V Common-Drain Dual N-Channel MOSFET

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>Trench Power MOSFET technology</li> <li>Ultra low <math>R_{SS(ON)}</math></li> <li>Common drain configuration for design simplicity</li> <li>RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>Battery protection switch</li> <li>Mobile device battery charging and discharging</li> </ul>	<p><b>Product Summary</b></p> <p><math>V_{SS}</math> 12V</p> <p><math>R_{SS(ON)}</math> (at <math>V_{GS}=4.5V</math>) &lt; 2.8m<math>\Omega</math></p> <p><math>R_{SS(ON)}</math> (at <math>V_{GS}=3.8V</math>) &lt; 3m<math>\Omega</math></p> <p><math>R_{SS(ON)}</math> (at <math>V_{GS}=3.1V</math>) &lt; 3.5m<math>\Omega</math></p> <p><math>R_{SS(ON)}</math> (at <math>V_{GS}=2.5V</math>) &lt; 4.2m<math>\Omega</math></p> <p><b>Typical ESD protection</b> HBM Class 2</p> 
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Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOCA33104E	AlphaDFN™ 2.98x1.49_10	Tape & Reel	8000

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Rating	Units
Source-Source Voltage	$V_{SS}$	12	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Source Current(DC) <sup>Note1</sup>	$I_S$	30	A
Source Current(Pulse) <sup>Note2</sup>	$I_{SM}$	130	
Power Dissipation <sup>Note1</sup>	$P_D$	3.1	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typical	Units
Maximum Junction-to-Ambient $t \leq 10\text{s}$	$R_{\theta JA}$	30	$^\circ\text{C/W}$
Maximum Junction-to-Ambient Steady-State		40	$^\circ\text{C/W}$

**Note 1.**  $I_S$  rated value is based on bare silicon. Mounted on 70mmx70mm FR-4 board.

**Note 2.** PW <10  $\mu\text{s}$  pulses, duty cycle 1% max.

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>SSS</sub>	Source-Source Breakdown Voltage	I <sub>S</sub> =250μA, V <sub>GS</sub> =0V Test Circuit 6	12			V
I <sub>SSS</sub>	Zero Gate Voltage Source Current	V <sub>SS</sub> =12V, V <sub>GS</sub> =0V Test Circuit 1 T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate leakage current	V <sub>SS</sub> =0V, V <sub>GS</sub> =±8V Test Circuit 2			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>SS</sub> =V <sub>GS</sub> , I <sub>S</sub> =250μA Test Circuit 3	0.4	0.75	1.2	V
R <sub>SS(ON)</sub>	Static Source to Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>S</sub> =5A Test Circuit 4 T <sub>J</sub> =125°C	1.6	2.25	2.8	mΩ
			2.1	3.1	3.9	
		V <sub>GS</sub> =3.8V, I <sub>S</sub> =5A Test Circuit 4	1.7	2.35	3	mΩ
		V <sub>GS</sub> =3.1V, I <sub>S</sub> =5A Test Circuit 4	1.8	2.55	3.5	mΩ
	V <sub>GS</sub> =2.5V, I <sub>S</sub> =5A Test Circuit 4	2	3	4.2	mΩ	
g <sub>FS</sub>	Forward Transconductance	V <sub>SS</sub> =5V, I <sub>S</sub> =5A Test Circuit 3		40		S
V <sub>FSS</sub>	Forward Source to Source Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V Test Circuit 5		0.6	1	V
<b>DYNAMIC PARAMETERS</b>						
R <sub>g</sub>	Gate resistance	f=1MHz		1.5		KΩ
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>G1S1</sub> =4.5V, V <sub>SS</sub> =6V, I <sub>S</sub> =5A		36		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>G1S1</sub> =4.5V, V <sub>SS</sub> =6V, R <sub>L</sub> =1.2Ω, R <sub>GEN</sub> =3Ω Test Circuit8		2.2		μs
t <sub>r</sub>	Turn-On Rise Time			5		μs
t <sub>D(off)</sub>	Turn-Off DelayTime			2.6		μs
t <sub>f</sub>	Turn-Off Fall Time			10.4		μs

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

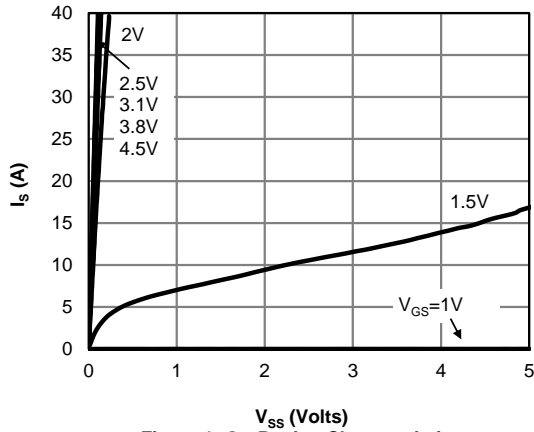


Figure 1: On-Region Characteristics

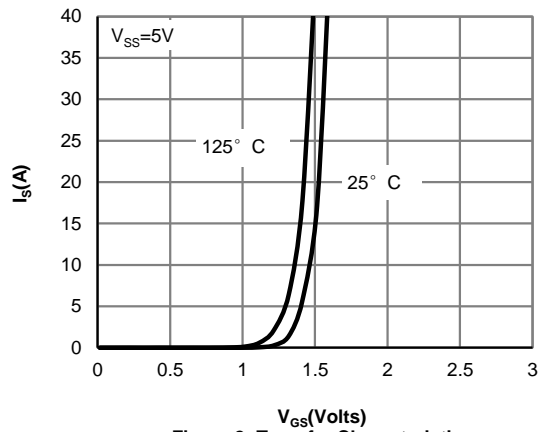


Figure 2: Transfer Characteristics

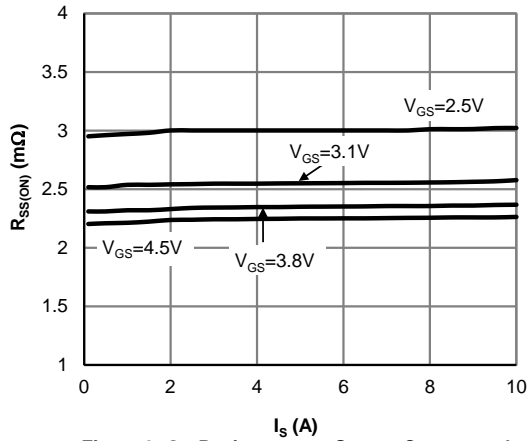


Figure 3: On-Resistance vs. Source Current and Gate Voltage

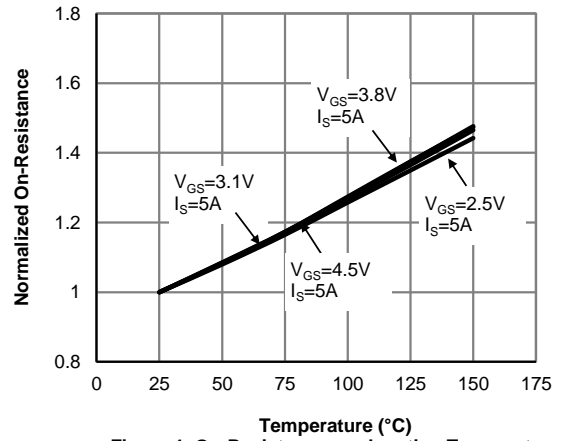


Figure 4: On-Resistance vs. Junction Temperature

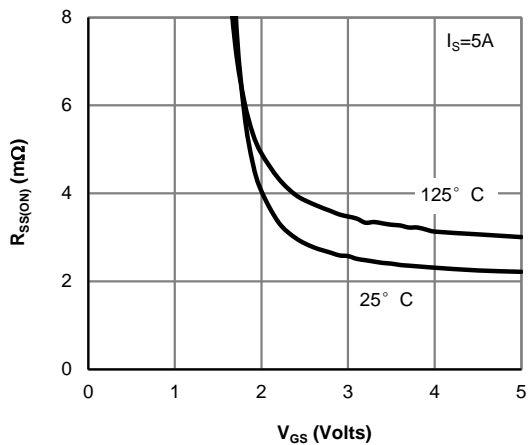


Figure 5: On-Resistance vs. Gate-Source Voltage

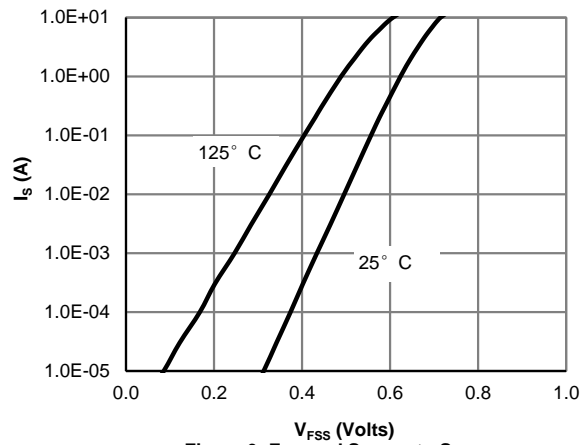


Figure 6: Forward Source to Source Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

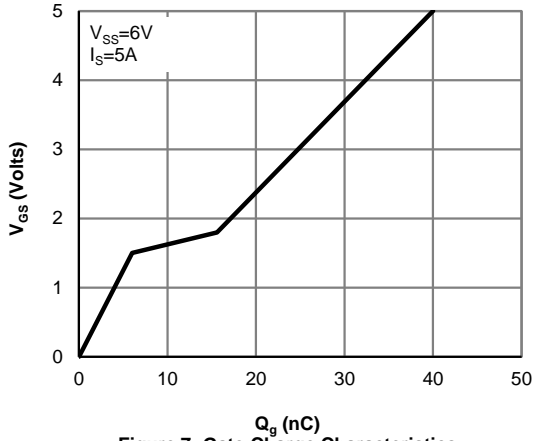


Figure 7: Gate-Charge Characteristics

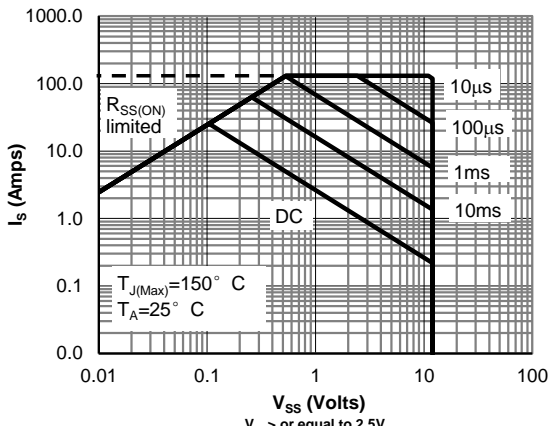


Figure 8: Maximum Forward Biased Safe Operating Area (Note1)

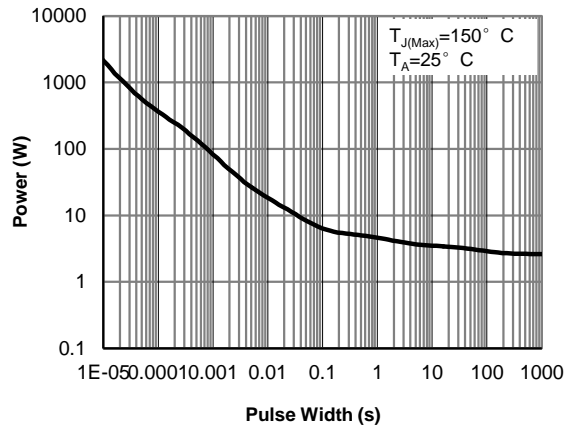


Figure 9: Single Pulse Power Rating Junction-to-Ambient (Note1)

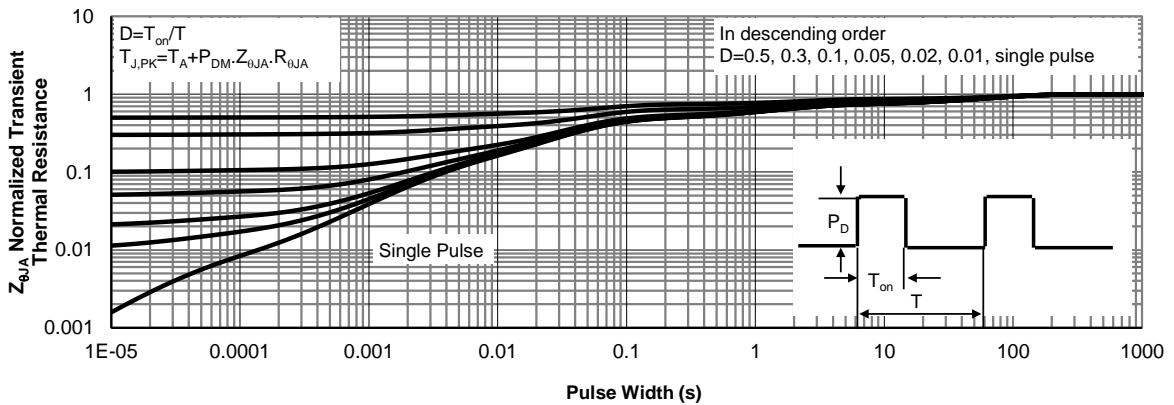


Figure 10: Normalized Maximum Transient Thermal Impedance (Note1)

